

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-25. (Canceled)

26. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; a first insulating layer, wherein a portion of said insulating layer is formed on said gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including ~~elements~~ impurities of a first conductivity type, formed over the semiconductor layer having the amorphous structure;

a second insulating layer comprising an inorganic material and formed on the semiconductor layer having the amorphous structure and the semiconductor layer containing the ~~elements~~ impurities of a first conductivity type so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer;

a wiring formed on the source and drain regions and a portion of the pixel electrode;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a portion of the first insulating layer on the storage capacitor wiring and a portion of the pixel electrode on the first insulating layer; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring;

wherein the input terminal portion includes a first layer comprising the same material as that

of the gate electrode and a second layer comprising the same material as that of the pixel electrode[[.]] , and

wherein the storage capacitor wiring is completely covered by the pixel electrode.

27. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; a first insulating layer, wherein a portion of said first insulating layer is formed on said gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including ~~elements~~ impurities of first conductivity type, formed over the semiconductor layer having the amorphous structure;

a second insulating layer comprising an inorganic material and formed on the semiconductor layer having the amorphous structure and the semiconductor layer containing the ~~elements~~ impurities of first conductivity type so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a portion of the first insulating layer on the storage capacitor wiring and a portion of the pixel electrode on the first insulating layer; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring;

wherein the input terminal portion comprises a first layer comprising the same material as that of the gate electrode and a second layer comprising the same material as that of the pixel

electrode in contact with the first layer through a single contact hole formed only in the first insulating layer[[]] , and

wherein the storage capacitor wiring is completely covered by the pixel electrode.

28. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; a first insulating layer, wherein a portion of said first insulating layer is formed on said gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including ~~elements~~ impurities of first conductivity type, formed over the semiconductor layer having the amorphous structure;

a pixel electrode formed in contact with the first insulating layer;

a second insulating layer comprising an inorganic material and formed on the pixel electrode and the semiconductor layer having the amorphous structure and the semiconductor layer containing the ~~elements~~ impurities of first conductivity type so as to be in contact with at least a part of the channel formation region;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a portion of the first insulating layer on the storage capacitor wiring and a portion of the pixel electrode on the first insulating layer; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring;

wherein the input terminal portion includes a first layer comprising the same material as that

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of the gate electrode and a second layer comprising the same material as that of the pixel electrode,
and

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion formed on at least an end portion thereof [[.]] , and

wherein the storage capacitor wiring is completely covered by the pixel electrode.

29. (Canceled)

30. (Currently Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; a first insulating layer, wherein a portion of said first insulating layer is formed on said gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including ~~elements~~ impurities of first conductivity type, formed over the semiconductor layer having the amorphous structure;

a second insulating layer comprising an inorganic material and formed on the semiconductor layer having the amorphous structure and the semiconductor layer containing the ~~elements~~ impurities of first conductivity type so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the first insulating layer;

a storage capacitor comprising a storage capacitor wiring comprising the same material as that of the gate electrode, a portion of the first insulating layer on the storage capacitor wiring and the pixel electrode on the first insulating layer; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring;

wherein the input terminal portion comprises a first layer comprising the same material as that of the gate electrode and a second layer comprising the same material as that of the pixel electrode in contact with the first layer through a single contact hole formed only in the first insulating layer, and

wherein each of the gate electrode, the storage capacitor wiring and the first layer has a tapered portion formed on at least an end portion thereof [[.]] , and

wherein the storage capacitor wiring is completely covered by the pixel electrode.
